

**HiPerFRED<sup>2</sup>**

$$V_{RRM} = 300V$$

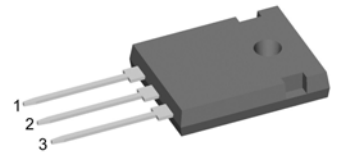
$$I_{FAV} = 2x \quad 40A$$

$$t_{rr} = 35ns$$

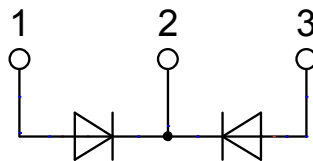
High Performance Fast Recovery Diode  
 Low Loss and Soft Recovery  
 Common Cathode

Part number

**DPG80C300HB**



Backside: cathode

**Features / Advantages:**

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

**Applications:**

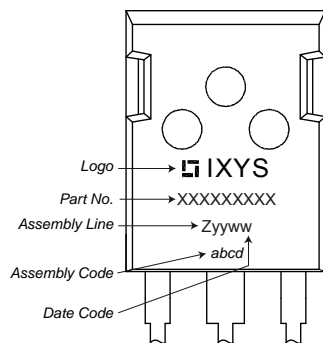
- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

**Package: TO-247**

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

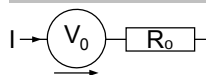
| Fast Diode |  |   |                              | Ratings |      |            |    |
|------------|--|---|------------------------------|---------|------|------------|----|
| Symbol     | Definition                                   | Conditions  | min.                         | typ.    | max. | Unit       |    |
| $V_{RSM}$  | max. non-repetitive reverse blocking voltage | $T_{VJ} = 25^{\circ}C$                                  |                              |         | 300  | V          |    |
| $V_{RRM}$  | max. repetitive reverse blocking voltage     | $T_{VJ} = 25^{\circ}C$                                  |                              |         | 300  | V          |    |
| $I_R$      | reverse current, drain current               | $V_R = 300 V$   | $T_{VJ} = 25^{\circ}C$       |         | 1    | $\mu A$    |    |
|            |  | $V_R = 300 V$   | $T_{VJ} = 150^{\circ}C$      |         | 0.2  | mA         |    |
| $V_F$      | forward voltage drop                         | $I_F = 40 A$  | $T_{VJ} = 25^{\circ}C$       |         | 1.36 | V          |    |
|            |  |   |                              |         | 1.71 | V          |    |
|            |  | $I_F = 80 A$  | $T_{VJ} = 150^{\circ}C$      |         | 1.07 | V          |    |
|            |  |   |                              |         | 1.44 | V          |    |
| $I_{FAV}$  | average forward current                      | $T_C = 135^{\circ}C$<br>rectangular $d = 0.5$           | $T_{VJ} = 175^{\circ}C$      |         | 40   | A          |    |
| $V_{FO}$   | threshold voltage                            | } for power loss calculation only                       | $T_{VJ} = 175^{\circ}C$      |         | 0.64 | V          |    |
| $r_F$      | slope resistance                             |   |                              |         | 9.2  | m $\Omega$ |    |
| $R_{thJC}$ | thermal resistance junction to case          |   |                              |         | 0.7  | K/W        |    |
| $R_{thCH}$ | thermal resistance case to heatsink          |   |                              | 0.25    |      | K/W        |    |
| $P_{tot}$  | total power dissipation                      |   | $T_C = 25^{\circ}C$          |         | 215  | W          |    |
| $I_{FSM}$  | max. forward surge current                   | $t = 10 ms; (50 Hz), sine; V_R = 0 V$                   | $T_{VJ} = 45^{\circ}C$       |         | 450  | A          |    |
| $C_J$      | junction capacitance                         | $V_R = 150 V$ $f = 1 MHz$                               | $T_{VJ} = 25^{\circ}C$       |         | 60   | pF         |    |
| $I_{RM}$   | max. reverse recovery current                | } $I_F = 40 A; V_R = 200 V$<br>$-di_F/dt = 200 A/\mu s$ | $T_{VJ} = 25^{\circ}C$       |         | 3    | A          |    |
| $t_{rr}$   | reverse recovery time                        |   | $T_{VJ} = \text{ }^{\circ}C$ |         |      | 8.5        | A  |
|            |  |   | $T_{VJ} = 25^{\circ}C$       |         |      | 35         | ns |
|            |  |   | $T_{VJ} = \text{ }^{\circ}C$ |         | 65   | ns         |    |

| Package TO-247 |                              |                            | Ratings |      |      |      |
|----------------|------------------------------|----------------------------|---------|------|------|------|
| Symbol         | Definition                   | Conditions                 | min.    | typ. | max. | Unit |
| $I_{RMS}$      | RMS current                  | per terminal <sup>1)</sup> |         |      | 70   | A    |
| $T_{VJ}$       | virtual junction temperature |                            | -55     |      | 175  | °C   |
| $T_{op}$       | operation temperature        |                            | -55     |      | 150  | °C   |
| $T_{stg}$      | storage temperature          |                            | -55     |      | 150  | °C   |
| <b>Weight</b>  |                              |                            |         | 6    |      | g    |
| $M_D$          | mounting torque              |                            | 0.8     |      | 1.2  | Nm   |
| $F_C$          | mounting force with clip     |                            | 20      |      | 120  | N    |

**Product Marking**

**Part number**

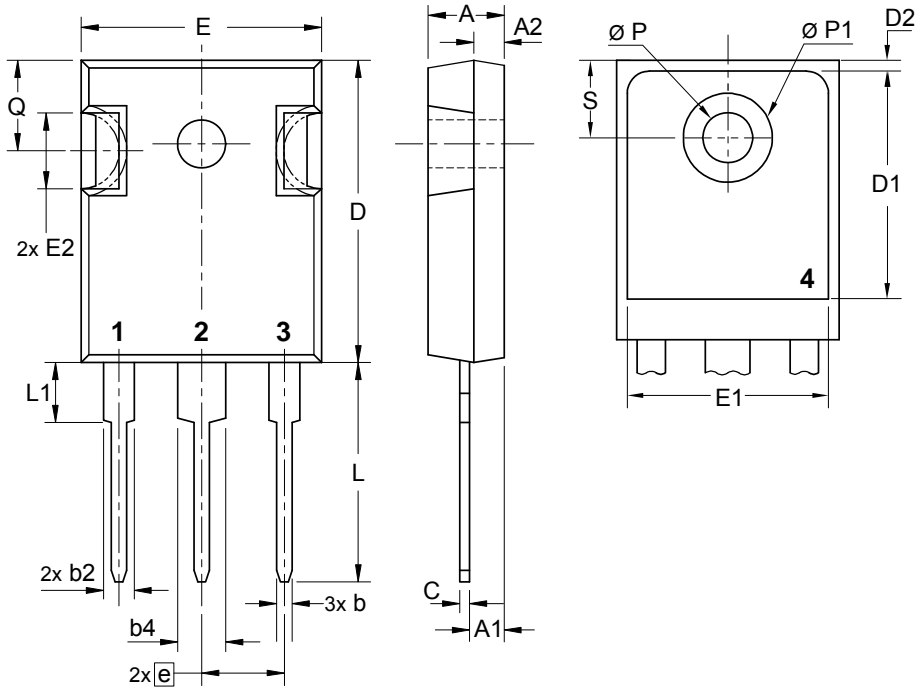
D = Diode  
 P = HiPerFRED  
 G = extreme fast  
 80 = Current Rating [A]  
 C = Common Cathode  
 300 = Reverse Voltage [V]  
 HB = TO-247AD (3)

| Ordering | Part Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-------------|--------------------|---------------|----------|----------|
| Standard | DPG80C300HB | DPG80C300HB        | Tube          | 30       | 506868   |

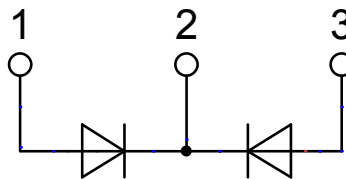
**Equivalent Circuits for Simulation**
*\* on die level*
 $T_{VJ} = 175\text{ °C}$ 

**Fast Diode**

|             |                    |      |    |
|-------------|--------------------|------|----|
| $V_{0\max}$ | threshold voltage  | 0.64 | V  |
| $R_{0\max}$ | slope resistance * | 7.6  | mΩ |

## Outlines TO-247



| Sym. | Inches    |       | Millimeter |       |
|------|-----------|-------|------------|-------|
|      | min.      | max.  | min.       | max.  |
| A    | 0.185     | 0.209 | 4.70       | 5.30  |
| A1   | 0.087     | 0.102 | 2.21       | 2.59  |
| A2   | 0.059     | 0.098 | 1.50       | 2.49  |
| D    | 0.819     | 0.845 | 20.79      | 21.45 |
| E    | 0.610     | 0.640 | 15.48      | 16.24 |
| E2   | 0.170     | 0.216 | 4.31       | 5.48  |
| e    | 0.215 BSC |       | 5.46 BSC   |       |
| L    | 0.780     | 0.800 | 19.80      | 20.30 |
| L1   | -         | 0.177 | -          | 4.49  |
| Ø P  | 0.140     | 0.144 | 3.55       | 3.65  |
| Q    | 0.212     | 0.244 | 5.38       | 6.19  |
| S    | 0.242 BSC |       | 6.14 BSC   |       |
| b    | 0.039     | 0.055 | 0.99       | 1.40  |
| b2   | 0.065     | 0.094 | 1.65       | 2.39  |
| b4   | 0.102     | 0.135 | 2.59       | 3.43  |
| c    | 0.015     | 0.035 | 0.38       | 0.89  |
| D1   | 0.515     | -     | 13.07      | -     |
| D2   | 0.020     | 0.053 | 0.51       | 1.35  |
| E1   | 0.530     | -     | 13.45      | -     |
| Ø P1 | -         | 0.29  | -          | 7.39  |



## Fast Diode

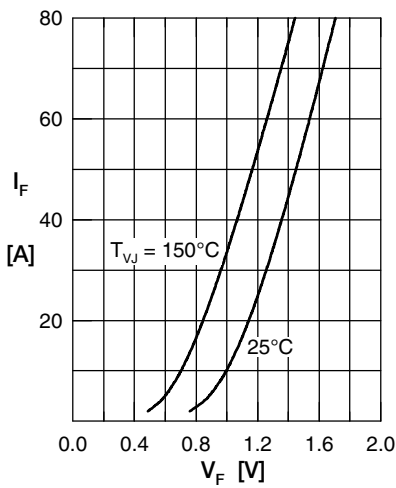


Fig. 1 Forward current  $I_F$  versus  $V_F$

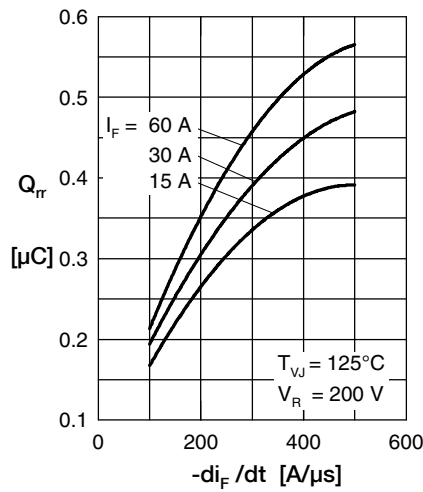


Fig. 2 Typ. reverse recov. charge  $Q_{rr}$  versus  $-di_F/dt$

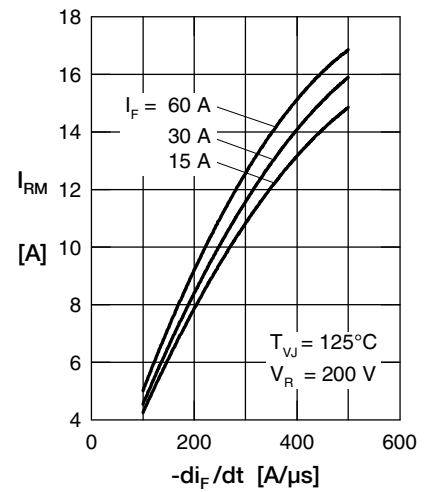


Fig. 3 Typ. reverse recov. current  $I_{RM}$  versus  $-di_F/dt$

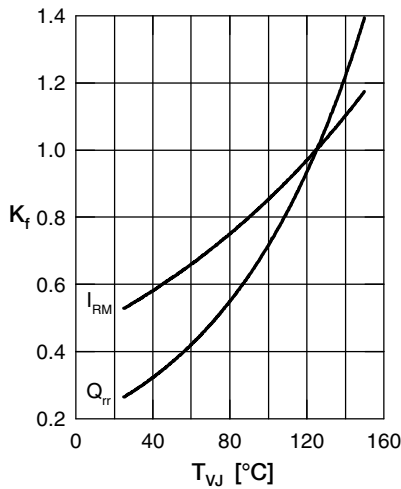


Fig. 4 Typ. dynamic parameters  $Q_{rr}$ ,  $I_{RM}$  versus  $T_{VJ}$

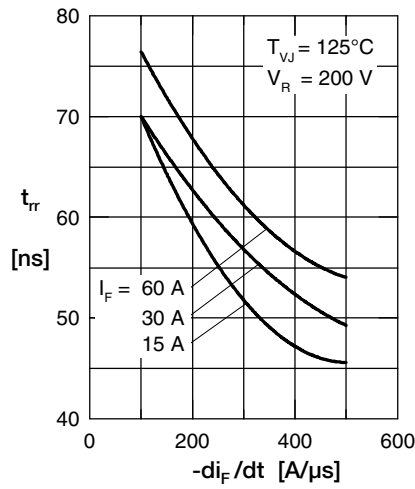


Fig. 5 Typ. reverse recov. time  $t_{rr}$  versus  $-di_F/dt$

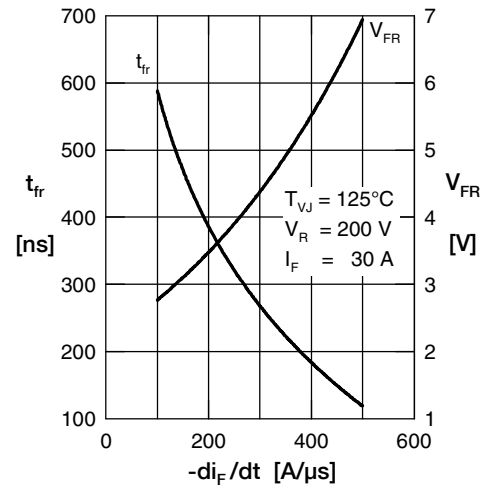


Fig. 6 Typ. forward recovery voltage  $V_{FR}$  & time  $t_{fr}$  versus  $di_F/dt$

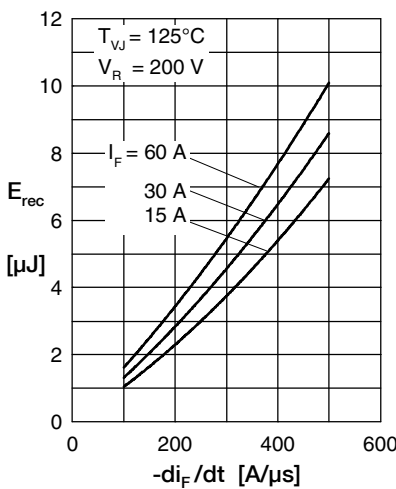


Fig. 7 Typ. recovery energy  $E_{rec}$  versus  $-di_F/dt$

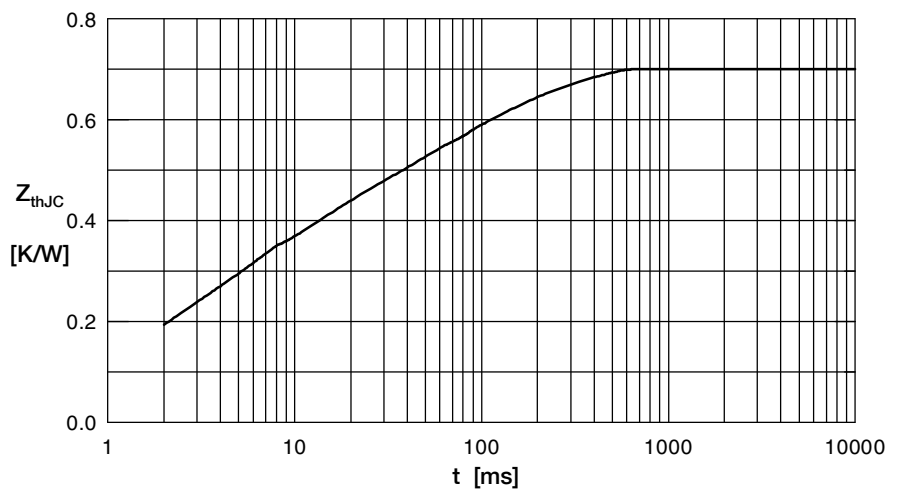


Fig. 8 Transient thermal impedance junction to case